Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	2.25	kV

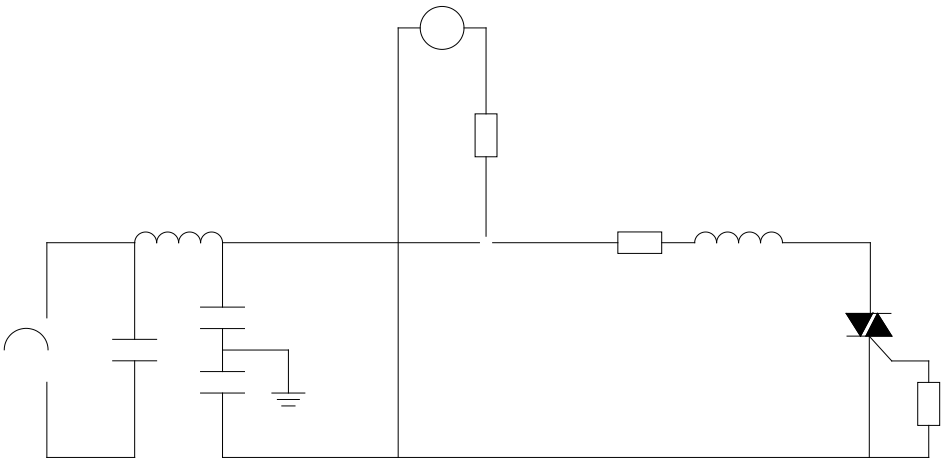
ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

ORDERING INFORMATION

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



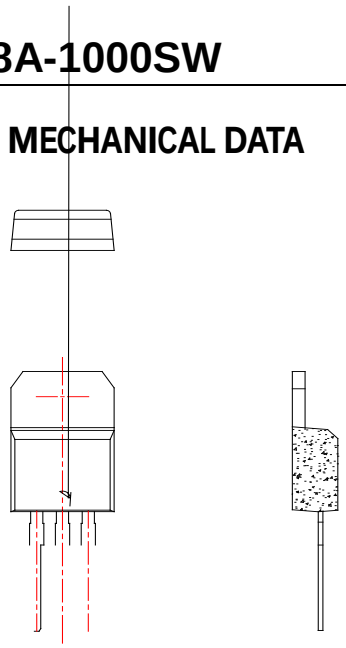
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT08A-1000SW	1000	10	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated
Oct.13, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



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